

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## OptiMOS™

OptiMOS™3 Power-Transistor, 100 V  
IPT020N10N3

## Data Sheet

Rev. 2.0  
Final

## 1 Description

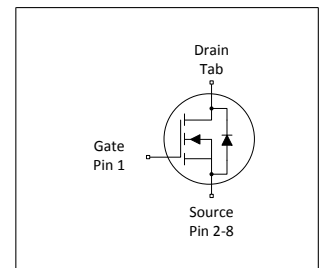
### Features

- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Extremely low on-resistance  $R_{DS(on)}$
- High current capability
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC <sup>1)</sup> for target application
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	100	V
$R_{DS(on),max}$	2	mΩ
$I_D$	300	A



Type / Ordering Code	Package	Marking	Related Links
IPT020N10N3	PG-HSOF-8-1	020N10N3	-

<sup>1)</sup> J-STD20 and JESD22

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## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	300 212	A	$T_C=25\text{ °C}$ <sup>1)</sup> $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	1200	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	800	mJ	$I_D=150\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	375	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

## 3 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance junction - case	$R_{thJC}$	-	0.2	0.4	K/W	-
Thermal resistance junction - ambient, minimal footprint	$R_{thJA}$	-	-	62	K/W	-
Thermal resistance junction - ambient, 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	40	K/W	-

<sup>1)</sup> See figure 3

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

## 4 Electrical characteristics

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	2.7	3.5	V	$V_{DS}=V_{GS}$ , $I_D=272\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.7 2.2	2 3.7	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=150\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=75\text{ A}$ ,
Gate resistance	$R_G$	-	1.9	2.9	$\Omega$	-
Transconductance	$g_{fs}$	125	250	-	S	$ V_{DS} >2 I_D /R_{DS(on)max}$ , $I_D=150\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	11200	14896	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	2010	2673	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{riss}$	-	69	138	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	34	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Rise time	$t_r$	-	58	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	84	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Fall time	$t_f$	-	18	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics <sup>1)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	48	-	nC	$V_{DD}=50\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	27	-	nC	$V_{DD}=50\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	42	-	nC	$V_{DD}=50\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	156	207	nC	$V_{DD}=50\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.3	-	V	$V_{DD}=50\text{ V}$ , $I_D=100\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	55	-	nC	$V_{DD}=50\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	300	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	1200	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.89	1	V	$V_{GS}=0\text{ V}, I_F=150\text{ A}, T_J=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	86	172	ns	$V_R=50\text{ V}, I_F=I_S, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	-	232	-	nC	$V_R=50\text{ V}, I_F=I_S, di_F/dt=100\text{ A}/\mu\text{s}$

## 5 Electrical characteristics diagrams

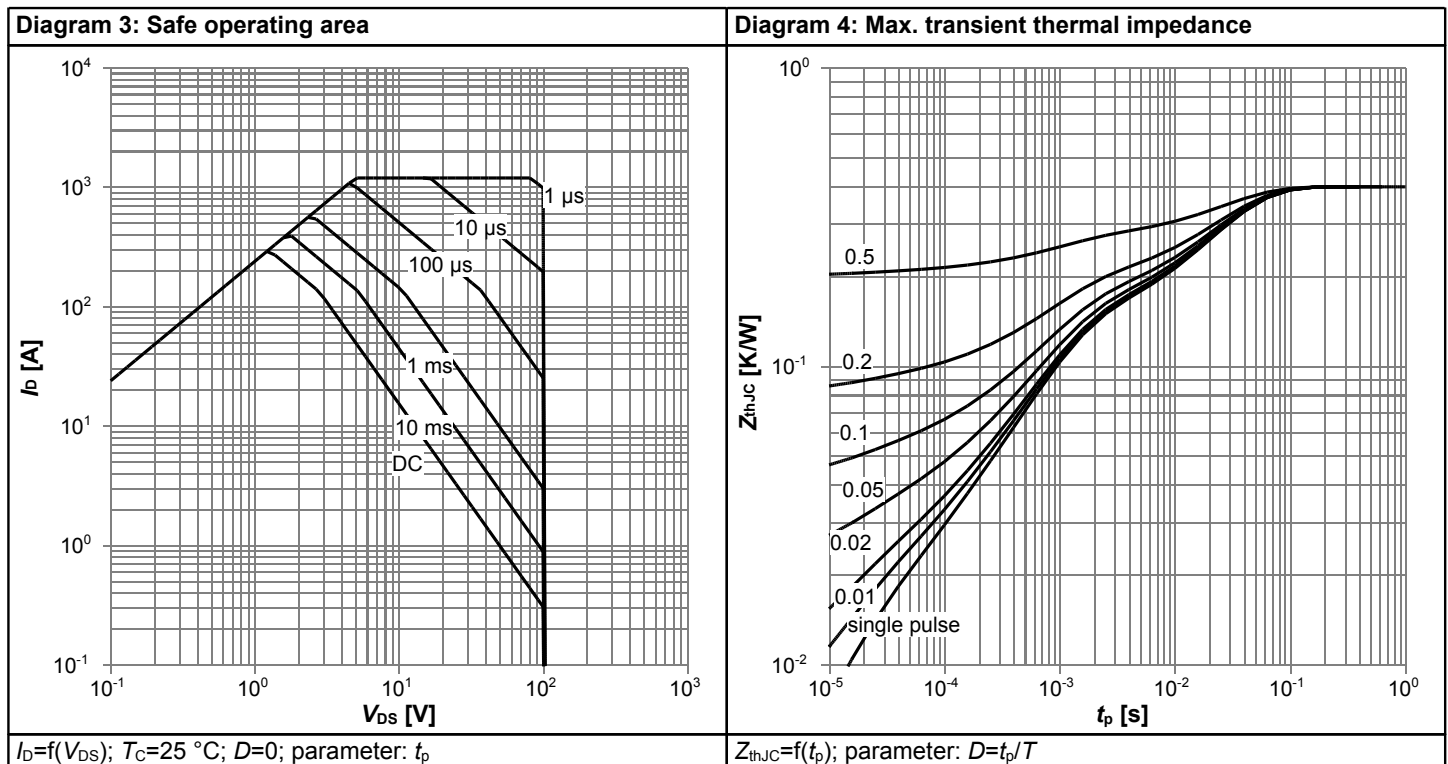
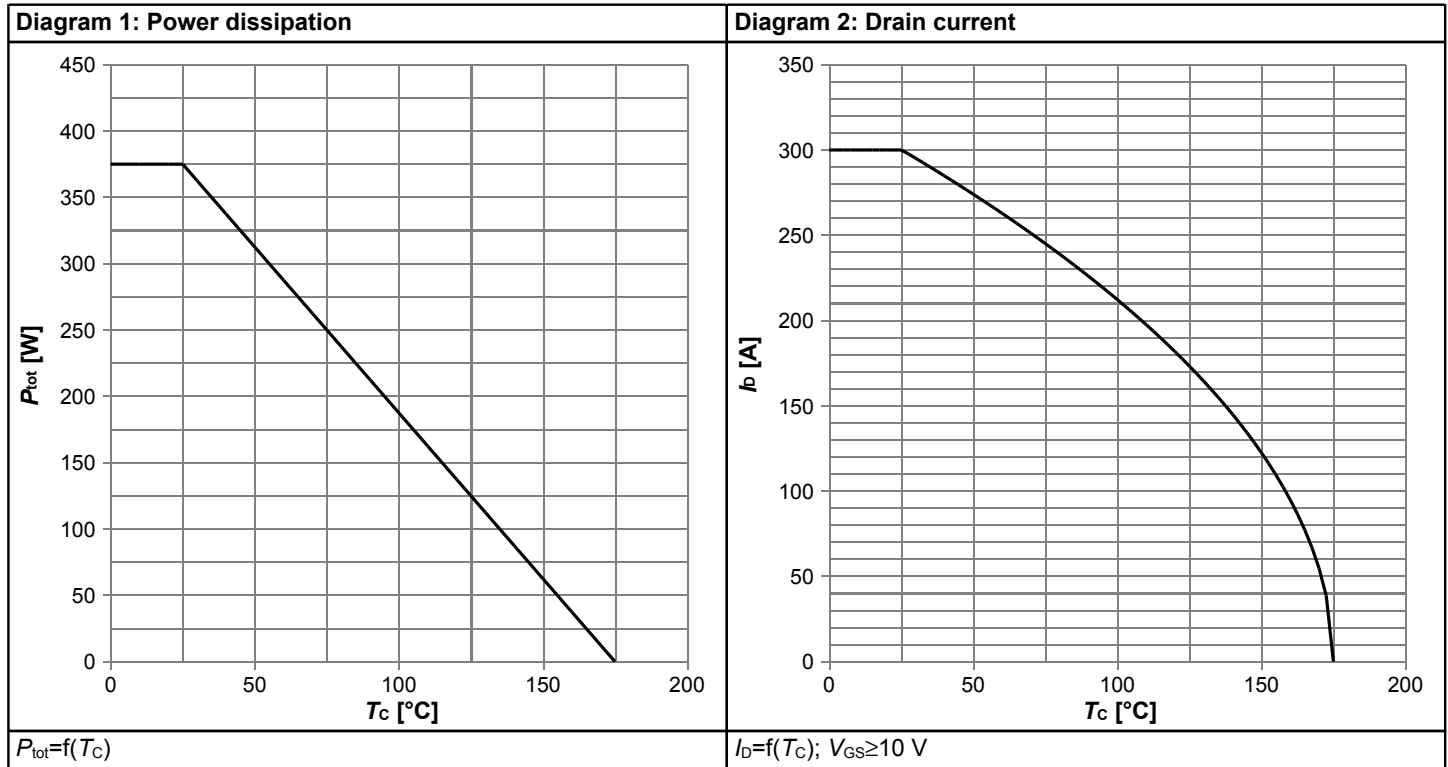
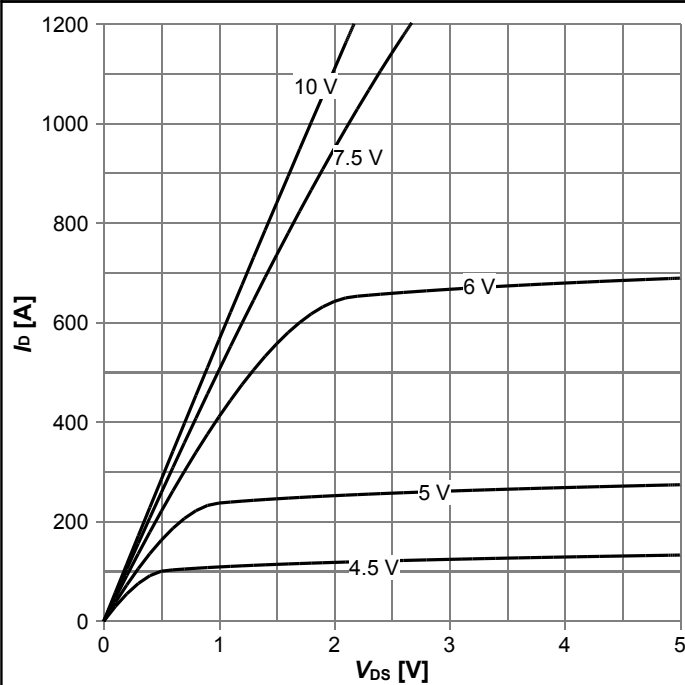
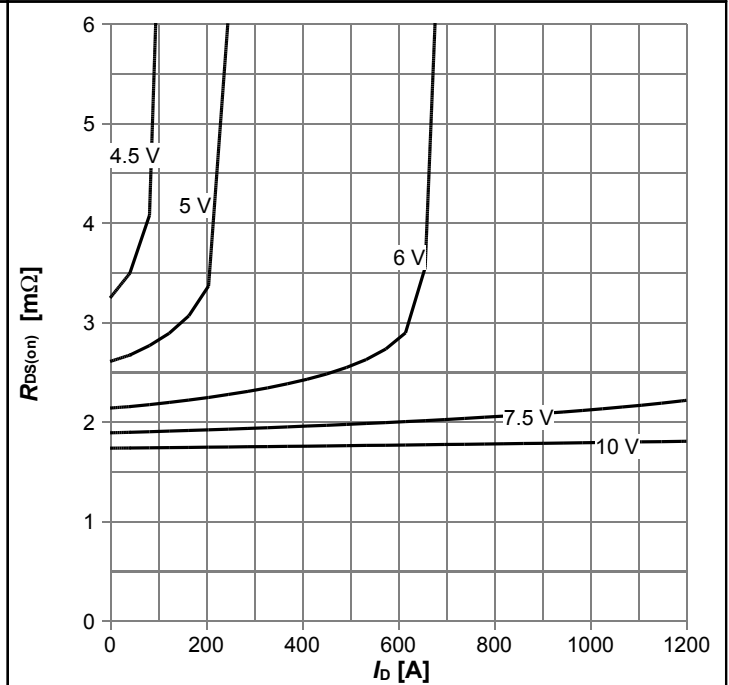


Diagram 5: Typ. output characteristics



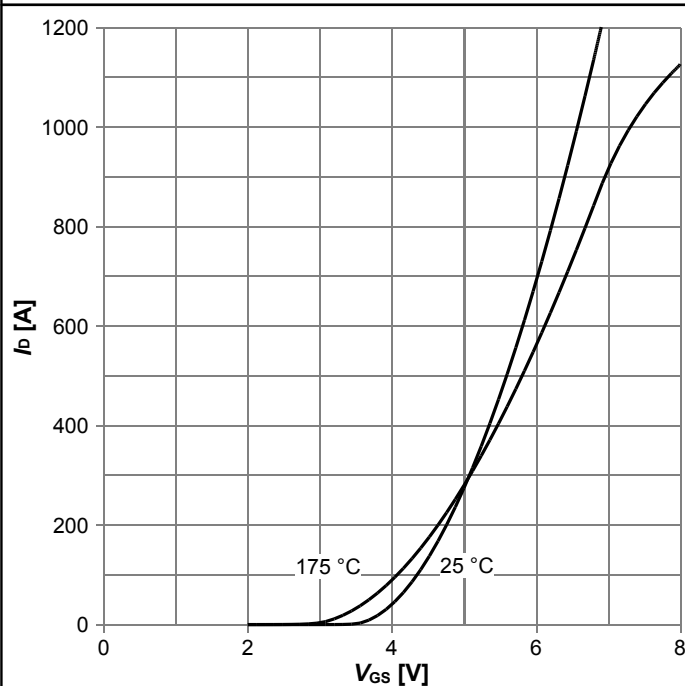
$I_D = f(V_{DS}); T_j = 25^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



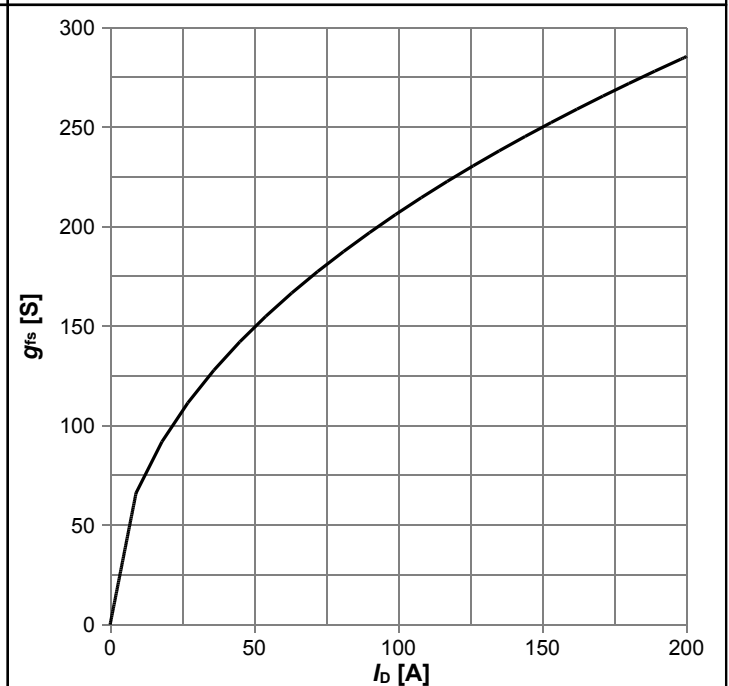
$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max};$  parameter:  $T_j$

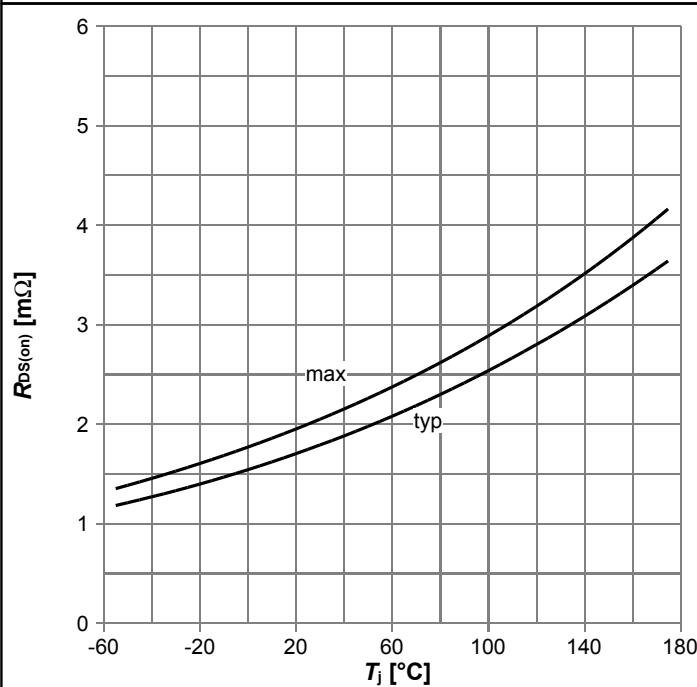
Diagram 8: Typ. forward transconductance



$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

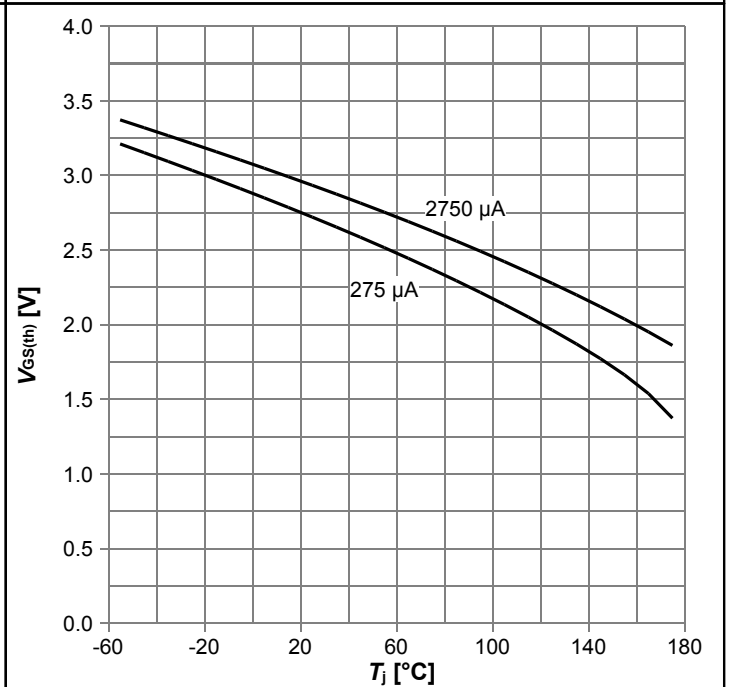


Diagram 9: Drain-source on-state resistance



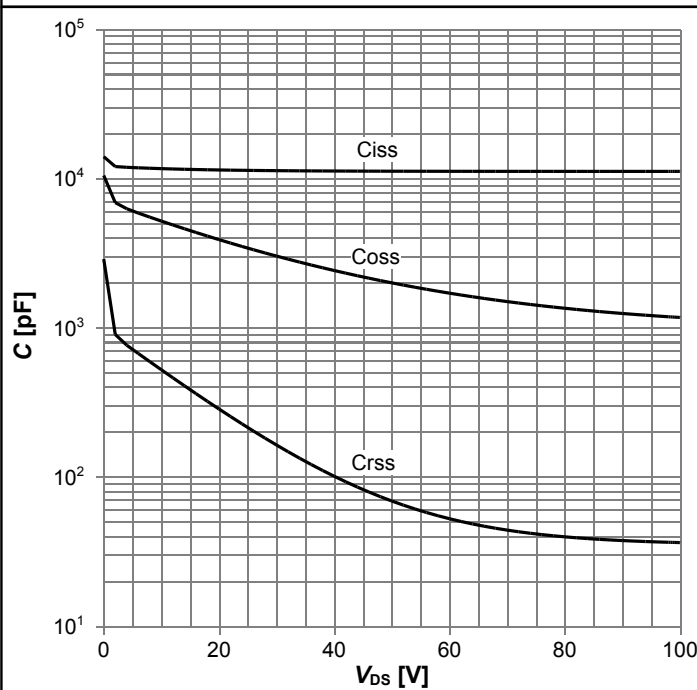
$R_{DS(on)}=f(T_j)$ ;  $I_D=150$  A;  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



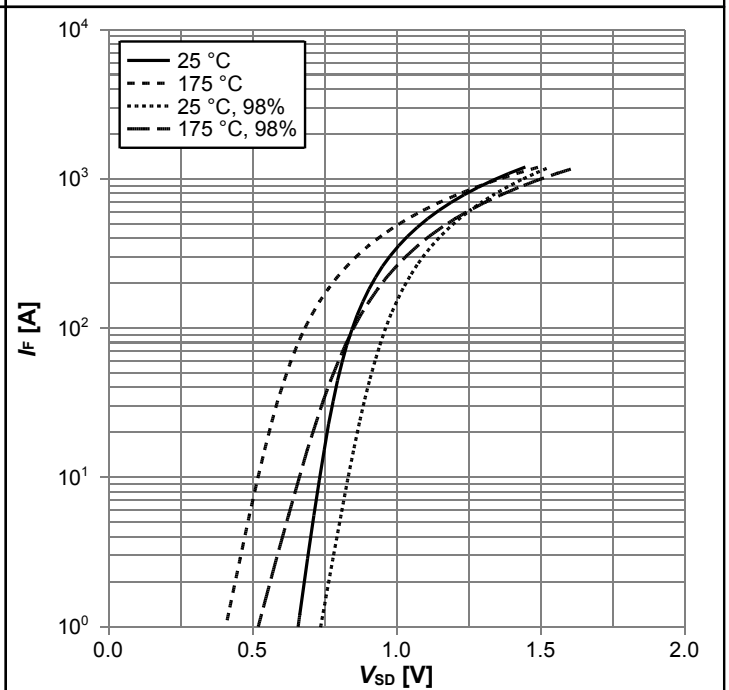
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



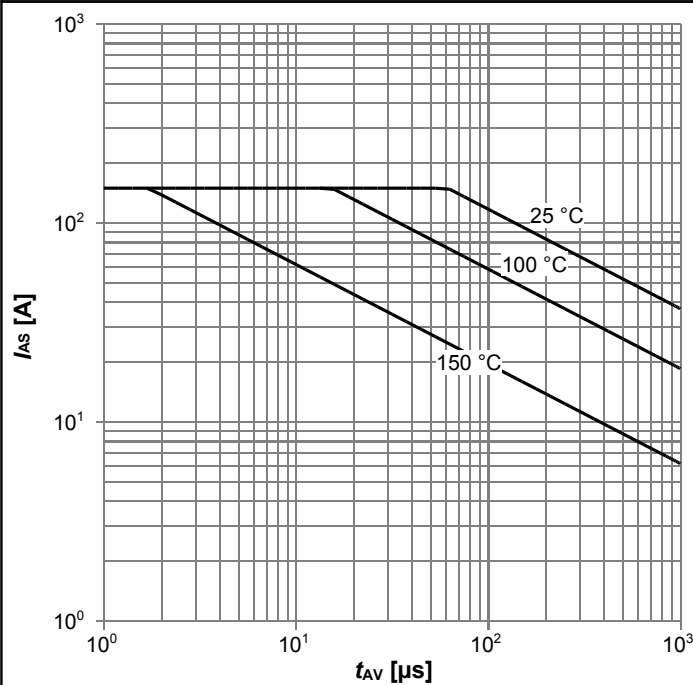
$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

Diagram 12: Forward characteristics of reverse diode



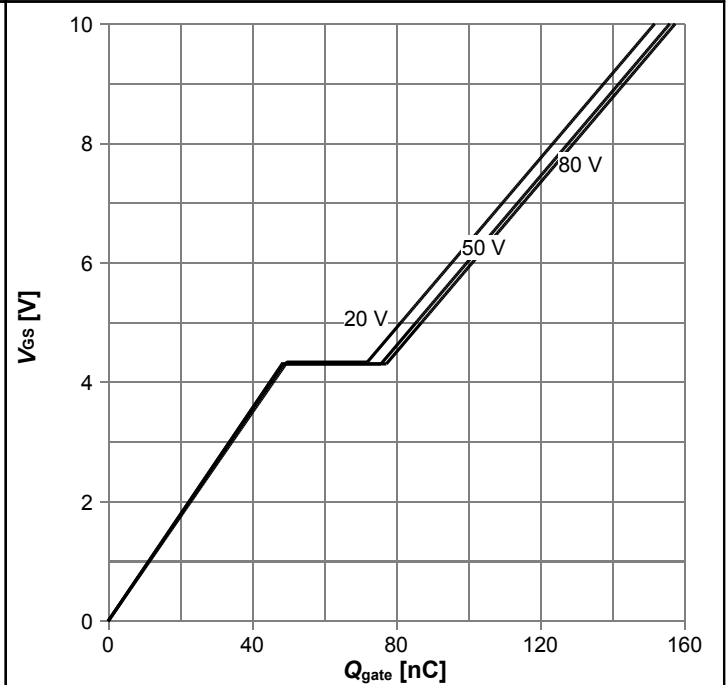
$I_F=f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics



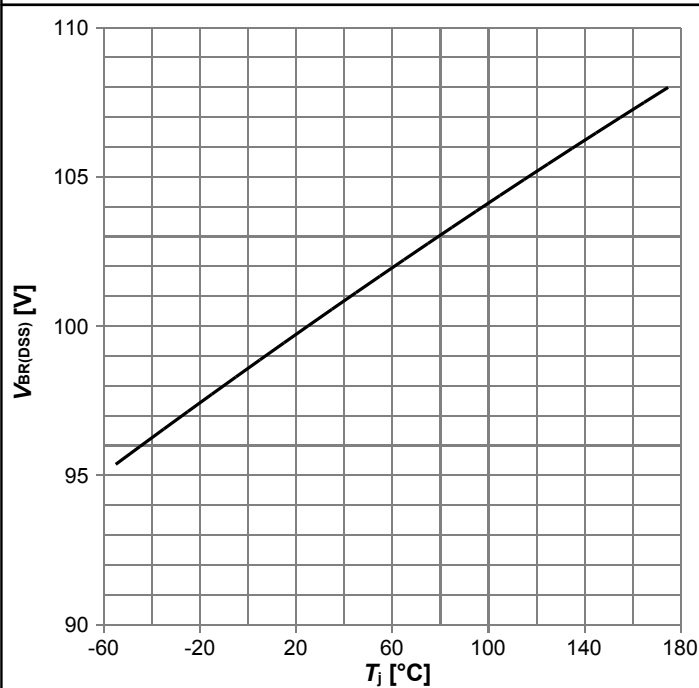
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



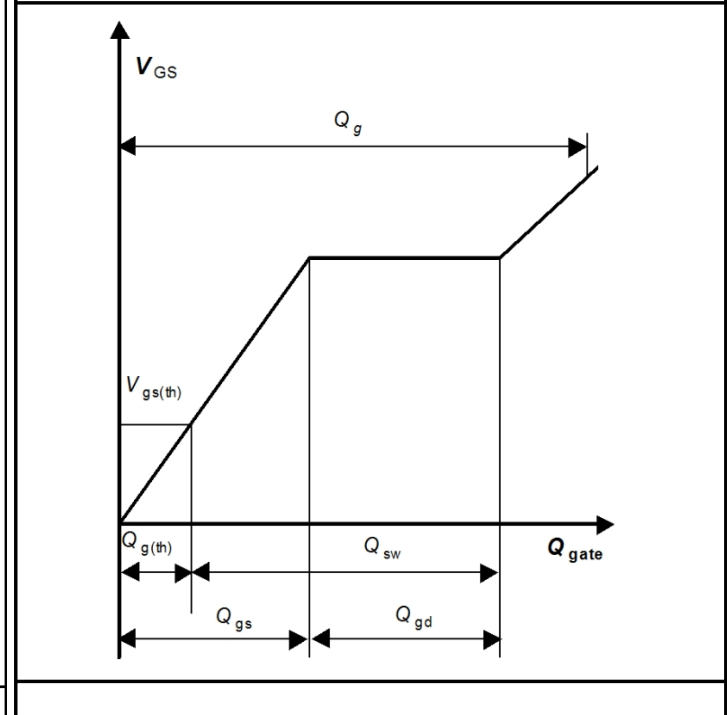
$V_{GS}=f(Q_{gate}); I_D=100$  A pulsed; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage

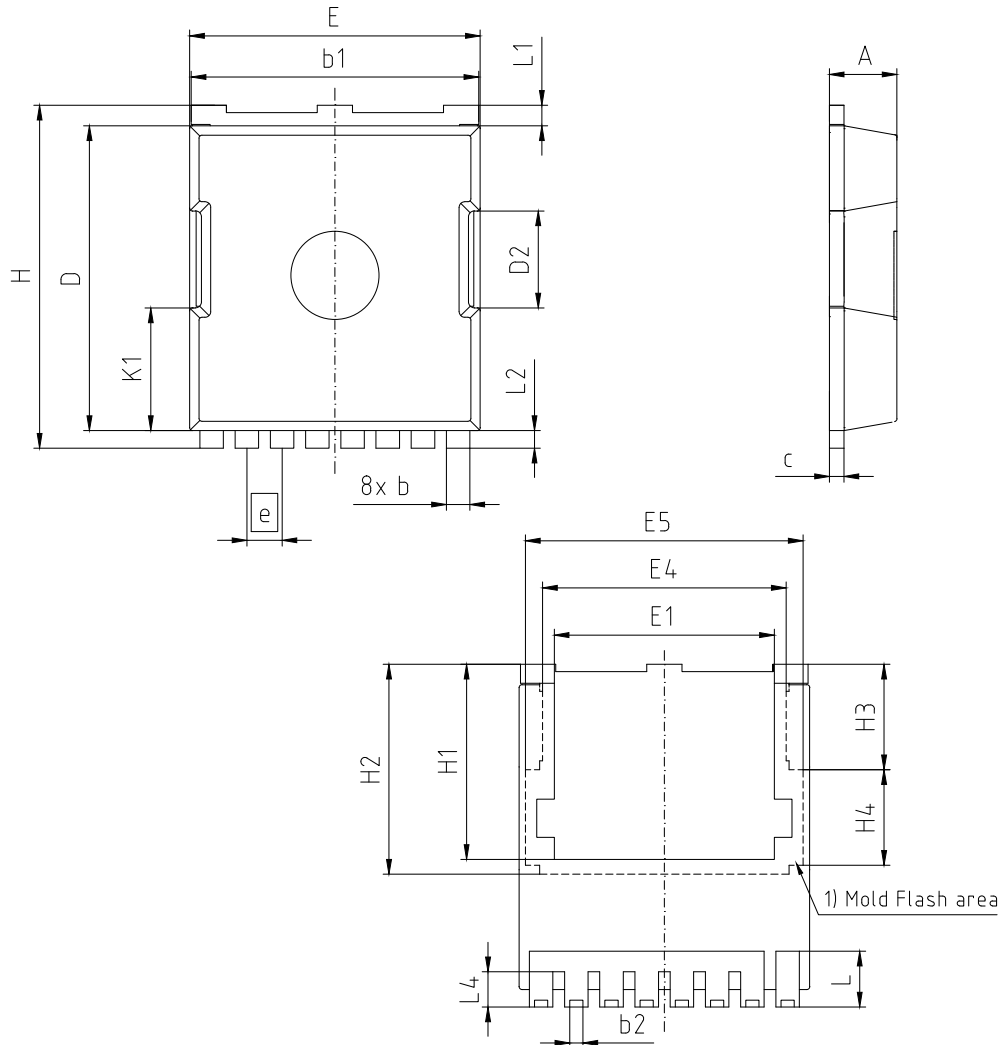


$V_{BR(DSS)}=f(T_j); I_D=1$  mA

Gate charge waveforms



6 Package Outlines



1) partially covered with Mold Flash

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.094
b	0.70	0.90	0.028	0.035
b1	9.70	9.90	0.382	0.390
b2	0.42	0.50	0.017	0.020
c	0.40	0.60	0.016	0.024
D	10.28	10.58	0.405	0.416
D2	3.30		0.130	
E	9.70	10.10	0.382	0.398
E1	7.50		0.295	
E4	8.50		0.335	
E5	9.46		0.372	
e	1.20 (BSC)		0.047 (BSC)	
H	11.48	11.88	0.452	0.468
H1	6.55	6.75	0.258	0.266
H2	7.15		0.281	
H3	3.59		0.141	
H4	3.26		0.128	
N	8		8	
K1	4.18		0.165	
L	1.60	2.10	0.063	0.083
L1	0.50	0.90	0.020	0.035
L2	0.50	0.70	0.020	0.028
L4	1.00	1.30	0.039	0.051

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SCALE  
0 2 4mm

EUROPEAN PROJECTION

ISSUE DATE  
14-06-2013

REVISION  
01

Figure 1 Outline PG-HSOF-8-1, dimensions in mm/inches

## Revision History

IPT020N10N3

**Revision: 2014-02-17, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-02-17	Release of final version

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